







SN74AHC1G14

SCLS321S - MARCH 1996 - REVISED FEBRUARY 2024

SN74AHC1G14 Single Schmitt-Trigger Inverter Gate

1 Features

- Operating range 2 V to 5.5 V
- Maximum t_{pd} of 10 ns at 5 V
- Low power consumption, 10-µA max I_{CC}
- ±8-mA output drive at 5 V
- Latch-up performance exceeds 250 mA per JESD 17

2 Applications

- **Barcode Scanners**
- Cable Solutions
- E-Books
- **Embedded PCs**
- Field Transmitter: Temperature or Pressure
- Fingerprint Biometrics
- HVAC: Heating, Ventilating, and Air Conditioning
- Network-Attached Storage (NAS)
- Sever Motherboard and PSU
- Software Defined Radios (SDR)
- TV: High Definition (HDTV), LCD, and Digital
- Video Communications Systems
- Wireless Data Access Cards, Headsets, Keyboards, Mice, and LAN Cards

3 Description

The SN74AHC1G14 device is a single inverter gate. The device performs the Boolean function $Y = \overline{A}$

Package Information

PART NUMBER PACKAGE ⁽¹⁾		PACKAGE SIZE(2)	BODY SIZE(3)
	DBV (SOT-23, 5)	2.8 mm × 2.8 mm	2.9 mm x 1.6 mm
SN74AHC1G14	DCK (SC-70, 5)	2 mm x 2.1 mm	2 mm × 1.25 mm
	DRL (SOT-553, 5)	1.6 mm x 1.6 mm	1.6 mm × 1.2 mm

- For all available packages, see the orderable addendum at the end of the data sheet.
- The package size (length × width) is a nominal value and includes pins, where applicable.
- The body size (length x width) is a nominal value and does not include pins.

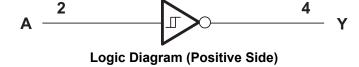


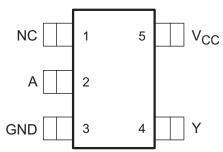


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4 Pin Configuration and Functions



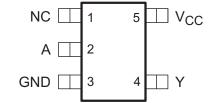


Figure 4-2. DCK Package 5-Pin SC70 Top View

Figure 4-1. DBV Package 5-Pin SOT-23 Top View

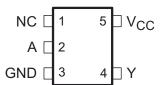


Figure 4-3. DRL Package 5-Pin SOT Top View

Table 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NO.	NAME	IIFE\/	DESCRIPTION
1	NC	_	No connect
2	Α	I	Data Input
3	GND	_	Ground
4	Y	0	Data Output
5	VCC	_	Power

(1) Signal Types: I = Input, O = Output, I/O = Input or Output



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
VI	Input voltage ⁽²⁾		-0.5	7	V
Vo	Output voltage ⁽²⁾		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-20	mA
I _{OK}	Output clamp current	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
Io	Continuous output current	$V_{O} = 0$ to V_{CC}		±25	mA
	Continuous current through V _{CC} or GND			±50	mA
Tj	Maximum junction temperature			150	°C
T _{stg}	Storage temperature	-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

			VALUE	UNIT
	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±1500	V
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	^{ESD)} discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2	5.5	V
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 2 V		-50	μA
I _{OH}	High-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		-4	mA
		$V_{CC} = 5 V \pm 0.5 V$		-8	ША
		V _{CC} = 2 V		50	μA
I _{OL}	Low-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		4	mA
		$V_{CC} = 5 V \pm 0.5 V$		8	ША
T _A	Operating free-air temperature		-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

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⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



5.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	DRL (SOT)	UNIT
		5 PINS	5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	278	289.2	271.8	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	180.5	205.8	116.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	184.4	176.2	89.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	115.4	117.6	17.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	183.4	175.1	89.4	°C/W
R _{0JC(bot)}	Junction-to-case (bot) thermal resistance	N/A	N/A	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST	V _{cc}	T	(= 25°C		T _A = -4	40°C to 85°C		OMMENDE 10°C to 12		UNIT
		CONDITIONS		MIN	TYP	MAX	MIN	TYP MA	MIN	TYP	MAX	
	5		3 V	1.2		2.2	1.2	2.	2 1.2		2.2	
V_{T+}	Positive-going input threshold voltage		4.5 V	1.75		3.15	1.75	3.1	1.75		3.15	V
	3		5.5 V	2.15		3.85	2.15	2.8	2.15		3.85	
	Negative-going		3 V	0.9		1.9	0.9	1.	0.9		1.9	
V_{T-}	input threshold		4.5 V	1.35		2.75	1.35	2.7	1.35		2.75	V
	voltage		5.5 V	1.65		3.35	1.65	3.3	1.65		3.35	
			3 V	0.3		1.2	0.3	1.	0.25		1.2	
ΔV_T	Hysteresis (V _{T+} – V _{T–})		4.5 V	0.4		1.4	0.4	1.	0.35		1.4	V
	- 1-/		5.5 V	0.5		1.6	0.5	1.	0.45		1.6	
		I _{OH} = -50 μA	2 V	1.9	2		1.9		1.9			
			3 V	2.9	3		2.9		2.9			
V_{OH}	High level output voltage		4.5 V	4.4	4.5		4.4		4.4			V
		I _{OH} = -4 mA	3 V	2.58			2.48		2.4			
		I _{OL} = -8 mA	4.5 V	3.94			3.8		3.7			
		Ι _{ΟΗ} = 50 μΑ	2 V		,	0.1		0.	1		0.1	
			3 V			0.1		0.	1		0.1	
V_{OL}	Low level output voltage		4.5 V			0.1		0.	1		0.1	V
	romago	I _{OH} = 4 mA	3 V			0.36		0.4	1		0.55	
		I _{OL} = 8 mA	4.5 V			0.36		0.4	1		0.55	
II	Input leakage current	V _I = 5.5 V or GND	0 V to 5.5 V			±0.1		±	1		±1	μA
I _{CC}	Supply current	V _I = V _{CC} or GND, I _O = 0	5.5 V			1		1)		10	μA
Ci	Input Capacitance	$V_I = V_{CC}$ or GND	5 V		2	10		1			10	pF

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5.6 Switching Characteristics, V_{CC} = 3.3 V \pm 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T _A = 25	s°C	T _A = -40°C 1	to 85°C	RECOMME T _A = -40° 125°	°C to	UNIT
				TYP	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	А	V	C ₁ = 15 pF	8.3	12.8	1	15	1	16	ns
t _{PHL}		' '	OL = 13 pr	8.3	12.8	1	15	1	16	ns
t _{PLH}	Α		C _L = 50 pF —	10.8	16.3	1	18.5	1	19.5	ns
t _{PHL}	Α	ı		10.8	16.3	1	18.5	1	19.5	ns

5.7 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

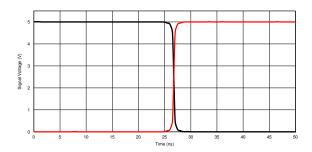
		0		•		, ,				,
PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T _A = 2	5°C	T _A = -40°C	to 85°C	RECOMME T _A = -40°C to		UNIT
	(INFOI)	(001701)	CAFACITANCE	TYP	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	A or B	V	C ₁ = 15 pF	5.5	8.6	1	10	1	11	ns
t _{PHL}	AOID	'	OL = 13 pr	5.5	8.6	1	10	1	11	ns
t _{PLH}	A or B	V	0 - 50 - 5	7	10.6	1	12	1	11	ns
t _{PHL}	AOID	ľ	$C_L = 50 \text{ pF}$	7	10.6	1	12	1	11	ns

5.8 Operating Characteristics

 V_{CC} = 5 V, T_A = 25°C

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	No load, f = 1 MHz	9	pF

5.9 Typical Characteristics



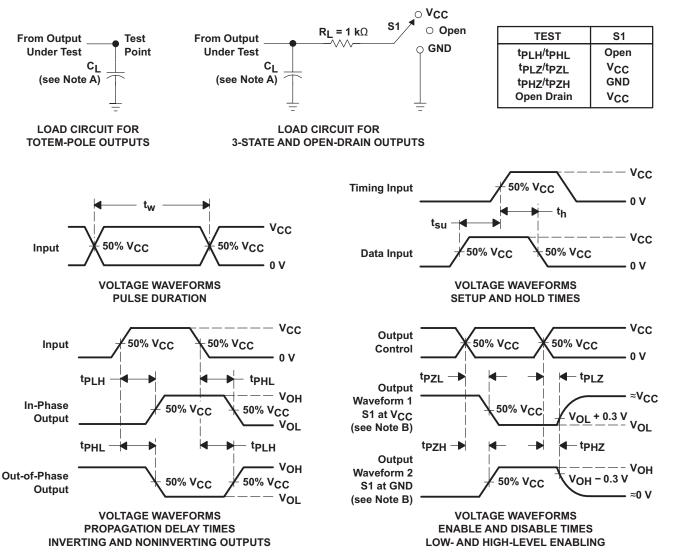
 $T_A = 25^{\circ}C, V_A = 5 V$

Figure 5-1. Response Time vs Output Voltage

Product Folder Links: SN74AHC1G14



6 Parameter Measurement Information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , $t_r \leq$ 3 ns, $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms



7 Detailed Description

7.1 Overview

The SN74AHC1G14 device is a single inverter gate. The device performs the Boolean function $Y = \overline{A}$.

The device functions as an independent inverter gate, but because of the Schmitt action, gates may have different input threshold levels for positive- (V_{T+}) and negative-going (V_{T-}) signals.

7.2 Functional Block Diagram

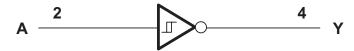


Figure 7-1. Logic Diagram (Positive Side)

7.3 Feature Description

The SN74AHC1G14 device has a wide operating V_{CC} range of 2 V to 5.5 V, which allows it to be used in a broad range of systems. The low propagation delay allows fast switching and higher speeds of operation. In addition, the low-power consumption makes this device a good choice for portable and battery power-sensitive applications.

7.4 Device Functional Modes

Table 7-1 lists the functional modes for SN74AHC1G14.

Table 7-1. Function Table

INPUT ⁽¹⁾ A	OUTPUT ⁽²⁾ Y
Н	L
L	Н

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
- (2) H = Driving High, L = Driving Low, Z = High Impedance State

Product Folder Links: SN74AHC1G14

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

Physically interactive interface elements like push buttons or rotary knobs offer simple and easy ways to interact with an electronic system. Many of these physical interface elements often have issues with bouncing, or where the physical conductive contact can connect and disconnect multiple times during a button push or release. This bouncing can cause one or more faulty transient signals to be passed during this transitional period. These faulty signals can be observed in many common applications, for example, a television remote with bouncing error can adjust the TV channel multiple times despite the button being pushed only once. To mitigate these faulty signals, we can use a Schmitt-trigger, or a device with hysteresis, to remove these faulty signals. Hysteresis allows a device to *remember* its history, and in this case, the SN74AHC1G14 uses this memory to debounce the signal of the physical element, or filter the faulty transient signals and pass only the valid signal each time the element is used. In this example, we show a push-button signal passed through an SN74AHC1G14 that is debounced and inverted to the microprocessor for push detection.

8.2 Typical Application

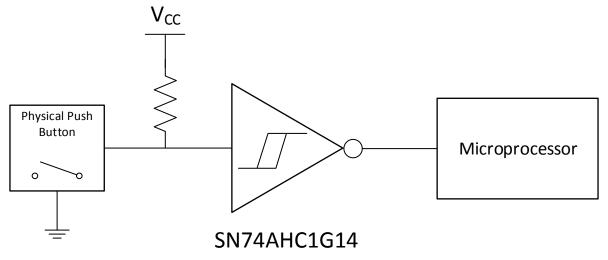


Figure 8-1. Switch Debouncer

8.2.1 Design Requirements

The SN74AHC1G14 device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The SN74AHC1G14 allows for performing logical Boolean functions with hysteresis using digital signals. All input signals must remain as close as possible to either 0 V or VCC for optimal operation.

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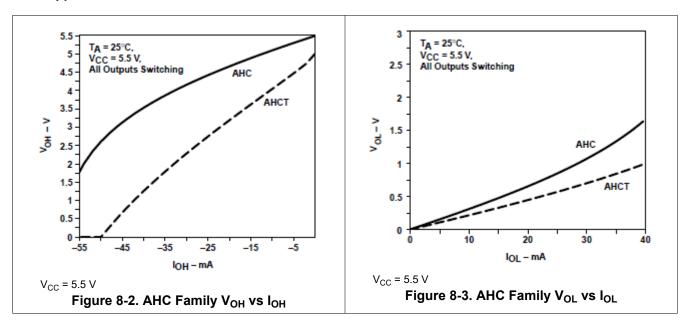
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8.2.2 Detailed Design Procedure

- 1. Recommended input conditions:
 - For rise time and fall time specifications, see $\Delta t/\Delta v$ in the Section 5.3 table.
 - For specified high and low levels, see V_{IH} and V_{IL} in the Section 5.3 table.
 - Inputs and outputs are overvoltage tolerant and can therefore go as high as 5.5 V at any valid V_{CC} .
- 2. Recommended output conditions:
 - Load currents must not exceed ±50 mA.
- 3. Frequency selection criterion:
 - The effects of frequency upon the power consumption of the device can be studied in CMOS Power Consumption and CPD Calculation, SCAA035.
 - Added trace resistance and capacitance can reduce maximum frequency capability; follow the layout practices listed in the Section 8.4.1 section.

8.2.3 Application Curves



8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the Section 5.3 table.

Each V_{CC} terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF bypass capacitor is recommended. If multiple pins are labeled V_{CC}, then a 0.01-μF or 0.022-µF capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 µF and 1 µF are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

8.4 Layout

8.4.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace, which results in the reflection. Not all PCB traces can be straight;

Product Folder Links: SN74AHC1G14



therefore some traces must turn corners. Figure 8-4 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

8.4.1.1 Layout Example

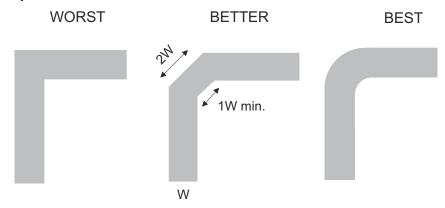


Figure 8-4. Trace Example



9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- CMOS Power Consumption and CPD Calculation, SCAA035
- Selecting the Right Texas Instruments Signal Switch, SZZA030

9.2 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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9.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision R (October 2023) to Revision S (February 2024)

Page

Updated thermal values for DBV package from RθJA = 225.7 to 278, RθJC(top) = 160.3 to 180.5, RθJB = 59.4 to 184.4, ΨJT = 41.0 to 115.4, ΨJB = 58.7 to 183.4, RθJC(bot) = N/A, all values in °C/W5

Changes from Revision Q (February 2014) to Revision R (October 2023)

- Added thermal values for DCK package: $R\theta JC(top) = 205.8$, $R\theta JB = 176.2$, $\Psi JT = 117.6$, $\Psi JB = 175.1$, RθJC(bot) = N/A, all values in °C/W5

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

Product Folder Links: SN74AHC1G14

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18-Dec-2024

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHC1G14DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(38SH, A143, A14G, A14J, A14L, A 14S)	Samples
SN74AHC1G14DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A14G	Samples
SN74AHC1G14DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A14G	Samples
SN74AHC1G14DBVT	OBSOLETE	SOT-23	DBV	5		TBD	Call TI	Call TI	-40 to 125	(A143, A14G, A14J, A14S)	
SN74AHC1G14DCK3	ACTIVE	SC70	DCK	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	AFY	Samples
SN74AHC1G14DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(1R9, AF3, AFG, AF J, AFL, AFS)	Samples
SN74AHC1G14DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF3	Samples
SN74AHC1G14DCKT	OBSOLETE	SC70	DCK	5		TBD	Call TI	Call TI	-40 to 125	(AF3, AFG, AFJ, AF S)	
SN74AHC1G14DCKTE4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF3	Samples
SN74AHC1G14DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF3	Samples
SN74AHC1G14DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	AFS	Samples
SN74AHC1G14DRLRG4	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	AFS	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

PACKAGE OPTION ADDENDUM

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Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74AHC1G14:

Automotive : SN74AHC1G14-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



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TAPE AND REEL INFORMATION



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHC1G14DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G14DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AHC1G14DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74AHC1G14DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AHC1G14DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G14DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G14DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3



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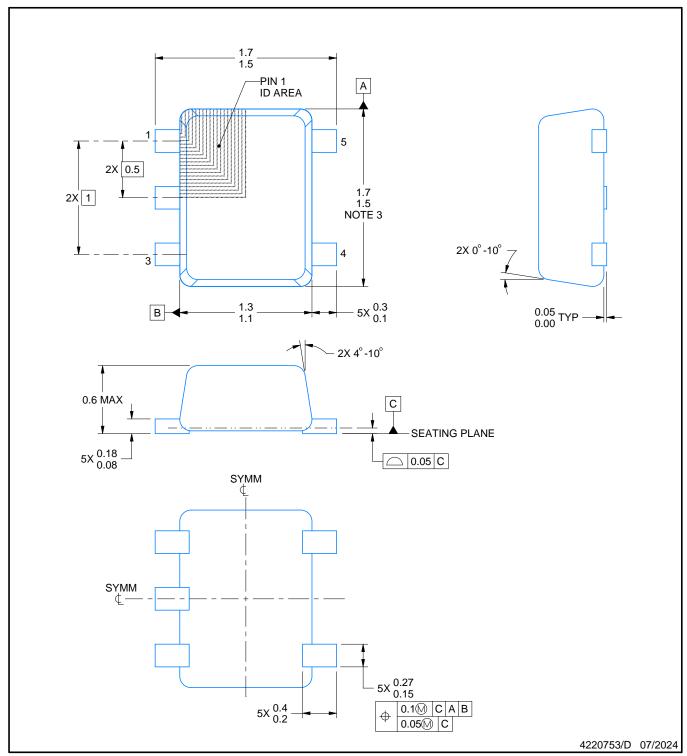


*All dimensions are nominal

7 til dillicionolo ale nominal								
Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0	
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0	
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0	
SN74AHC1G14DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0	
SN74AHC1G14DCKR	SC70	DCK	5	3000	202.0	201.0	28.0	
SN74AHC1G14DCKR	SC70	DCK	5	3000	210.0	185.0	35.0	
SN74AHC1G14DCKR	SC70	DCK	5	3000	180.0	180.0	18.0	
SN74AHC1G14DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0	
SN74AHC1G14DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0	
SN74AHC1G14DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0	



PLASTIC SMALL OUTLINE

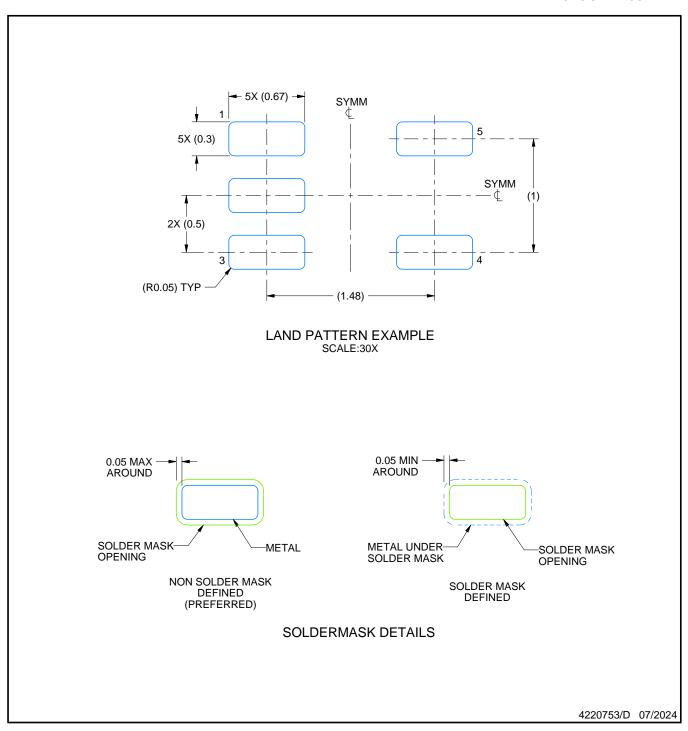


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1



PLASTIC SMALL OUTLINE

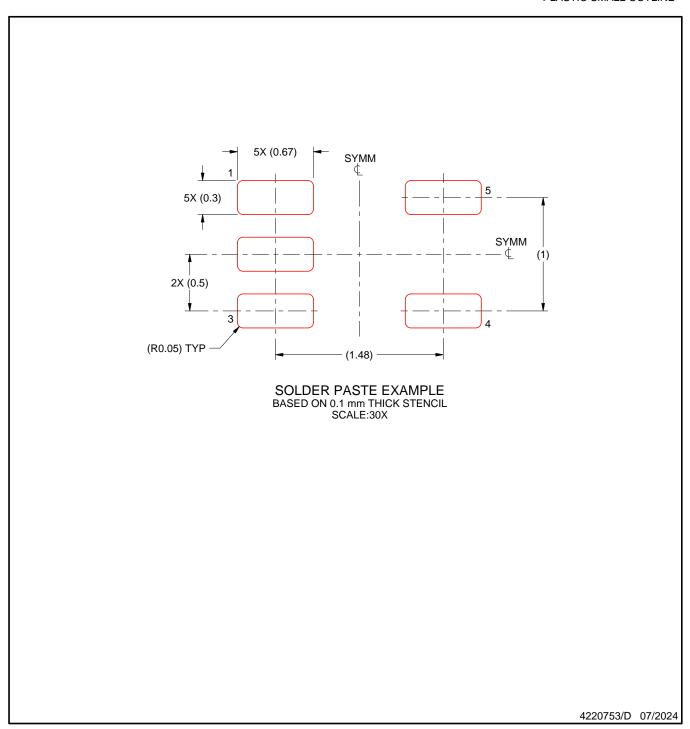


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side





NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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